

DH254 Hall-effect sensor is a temperature stable, stress-resistant, Low Tolerance of Sensitivity micro-power switch. Superior high-temperature performance is made possible through a dynamic offset cancellation that utilizes chopper-stabilization. This method reduces the offset voltage normally caused by device over molding, temperature dependencies, and thermal stress.

DH254 is special made for low operation voltage, 1.65V, to active the chip which is includes the following on a single silicon chip: voltage regulator, Hall voltage generator, small-signal amplifier, chopper stabilization, Schmitt trigger, CMOS output driver. Advanced CMOS wafer fabrication processing is used to take advantage of low-voltage requirements, component matching, very low input-offset errors, and small component geometries. This device requires the presence of unipolar magnetic fields for operation.

The package type is in a Halogen Free version has been verified by third party Lab.

Features and Benefits

- CMOS Hall IC Technology
- Strong RF noise protection
- 1.65 to 6V for battery-powered applications
- Operation down to 1.65V, Unipolar Hall Switch Micro power consumption
- High Sensitivity for reed switch replacement applications
- Low sensitivity drift in crossing of Temp. range
- Ultra Low power consumption at 5uA (Avg)
- High ESD Protection, HBM > ±4KV(min)
- Totem-pole output

Applications

- Solid state switch
- Handheld Wireless Handset Awake Switch (Flip Cell/PHS Phone/Note Book/Flip Video Set)
- Magnet proximity sensor for reed switch replacement in low duty cycle applications
- Water Meter
- PDA
- PDVD
- NB
- Pad PC

Absolute Maximum Ratings At($T_a=25^\circ\text{C}$)

Characteristics		Values	Unit
Supply voltage, (V_{DD})		7	V
Output Voltage, (V_{out})		7	V
Reverse Voltage, (V_{DD}) (V_{out})		-0.3	V
Magnetic flux density		Unlimited	Gauss
Output current, (I_{out})		1	mA
Operating temperature range, (T_a)		-40 to +85	$^\circ\text{C}$
Storage temperature range, (T_s)		-65 to +150	$^\circ\text{C}$
Maximum Junction Temp, (T_j)		150	$^\circ\text{C}$
Thermal Resistance	(θ_{JA}) VK / SN	227 / 540	$^\circ\text{C}/\text{W}$
	(θ_{JC}) VK / SN	49 / 390	$^\circ\text{C}/\text{W}$
Package Power Dissipation, (P_D) VK / SN		550 / 230	mW

Note: Exceeding the absolute maximum ratings may cause permanent damage. Exposure to absolute maximum-rated conditions for extended periods may affect device reliability.

Electrical Specifications

DC Operating Parameters : $T_a=25^\circ\text{C}$, $V_{DD}=1.8\text{V}$

Parameters	Test Conditions	Min	Typ	Max	Units
Supply Voltage, (V_{DD})	Operating	1.65		6	Volts
Supply Current, (I_{DD})	Awake State		1.4	3	mA
	Sleep State		3.6	7	μA
	Average		5	10	μA
Output Leakage	Output off			1	μA
Output High Voltage, (V_{OH})	$I_{OUT}=0.5\text{mA}$ (Source)	$V_{DD}-0.2$			V
Output Low Voltage, (V_{OL})	$I_{OUT}=0.5\text{mA}$ (Sink)			0.2	V
Awake mode time, (T_{aw})	Operating		40	80	μs
Sleep mode time, (T_{sl})	Operating		40	80	mS
Duty Cycle, (D, C)			0.1		%
Electro-Static Discharge	HBM	4			KV
Operating Point -(Bop),	N pole to branded side, $B > \text{BOP}$, Oout On		30	50	Gauss
Release Point-(Brp)	N pole to branded side, $B < \text{BRP}$, Vout Off	10	20		Gauss
Hysteresis-(BHYS)	$ \text{BOP}_x - \text{BRP}_x $		10		Gauss

Sensor Location, package dimension and marking
DH254 Package

